

## Dual N-Channel 40 V (D-S) Super Junction MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ) (Typ.)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)
40	6.6 at V <sub>GS</sub> = 10 V	48	13 nC
	9.7 at V <sub>GS</sub> = 4.5 V		

### FEATURES

- DT-SJ Power MOSFET
- 100 % R<sub>g</sub> and UIS tested
- Integrated MOSFET half-bridge power stage

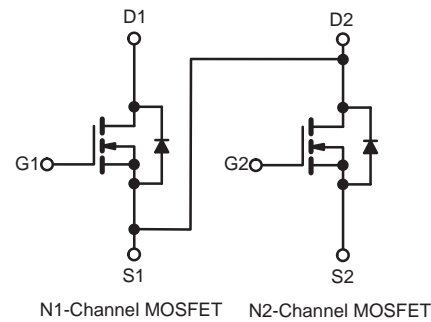
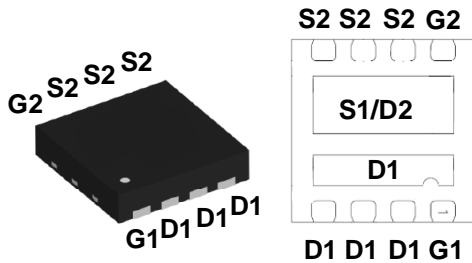


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COMPLIANT

### APPLICATIONS

- Synchronous Rectification
- Motor Drives and Uninterruptible Power Supplies

DFN3x3 Asymmetric Dual Pin Configuration



ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	40	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	
Continuous Drain Current (T <sub>J</sub> = 175 °C)	T <sub>C</sub> = 25 °C	I <sub>D</sub>	48	A
	T <sub>C</sub> = 100 °C		32	
Pulsed Drain Current		I <sub>DM</sub>	160	
Single Avalanche Energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	50	mJ
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	30 <sup>b,c</sup>	W
	T <sub>C</sub> = 100 °C		21.2 <sup>b,c</sup>	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Soldering Recommendations (Peak Temperature)			260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) <sup>b,d</sup>	t ≤ 10 s	R <sub>thJA</sub>	30	°C/W
Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	4.2	

Notes:

- T<sub>C</sub> = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under steady state conditions is 40 °C/W.

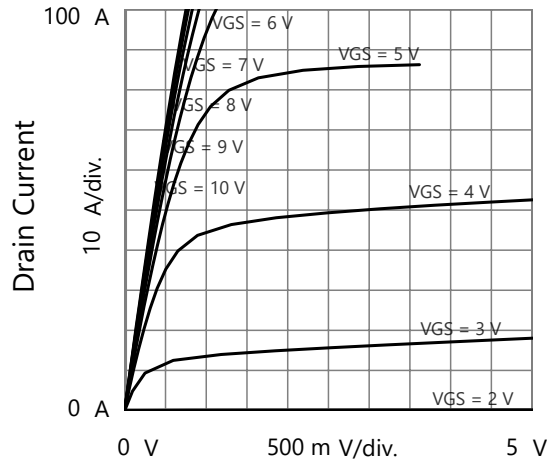
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	40	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1	-	2.5	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 32\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	-	-	10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 10\text{ V}, V_{GS} = 10\text{ V}$	48	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$	-	6.6	9	m $\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 7\text{ A}$	-	9.7	15	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 5\text{ V}, I_D = 10\text{ A}$	-	40	-	S
<b>Dynamic <sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 20\text{ V}, f = 1\text{ MHz}$	-	712	-	pF
Output Capacitance	$C_{oss}$		-	423	-	
Reverse Transfer Capacitance	$C_{rss}$		-	26	-	
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = 20\text{ V}, V_{GS} = 10\text{ V}, I_D = 10\text{ A}$	-	13	-	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$		-	1.3	-	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$		-	2.4	-	
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	-	6	-	$\Omega$
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DS} = 20\text{ V}, I_D = 10\text{ A}, R_g = 2.5\text{ }\Omega$ $V_{GS} = 10\text{ V}$	-	10	-	ns
Rise Time <sup>c</sup>	$t_r$		-	9	-	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$		-	52	-	
Fall Time <sup>c</sup>	$t_f$		-	27	-	
<b>Drain-Source Body Diode Ratings and Characteristics <sup>b</sup> (<math>T_C = 25\text{ }^\circ\text{C}</math>)</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$	-	-	48	A
Pulsed Current ( $t = 100\text{ }\mu\text{s}$ )	$I_{SM}$		-	-	160	A
Forward Voltage <sup>a</sup>	$V_{SD}$	$I_F = 100\text{ A}, V_{GS} = 0\text{ V}$	-	-	1.2	V
Reverse Recovery Time	$t_{rr}$	$I_F = 10\text{ A}, di/dt = 300\text{ A}/\mu\text{s}$	-	19	-	ns
Reverse Recovery Charge	$Q_{rr}$		-	10	-	nC

**Notes**

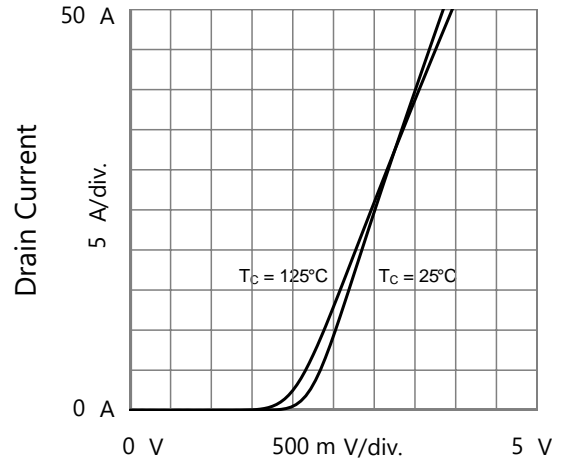
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 b. Guaranteed by design, not subject to production testing.  
 c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

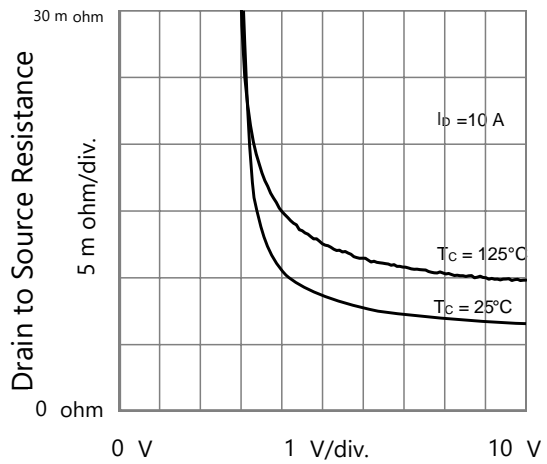
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



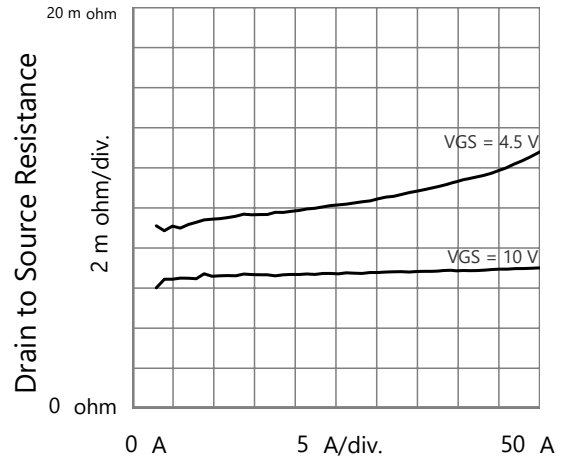
Drain to Source Voltage  
Output Characteristics



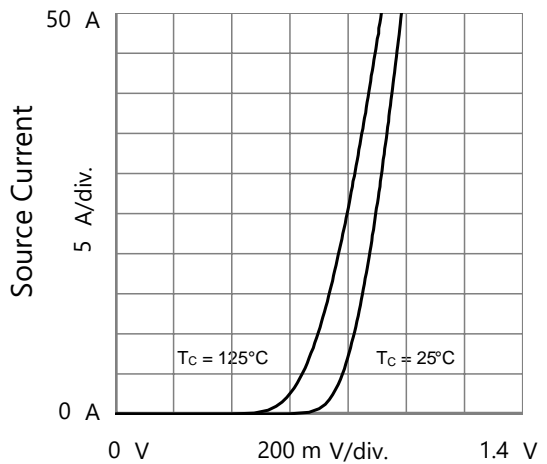
Gate to Source Voltage  
Transfer Characteristics



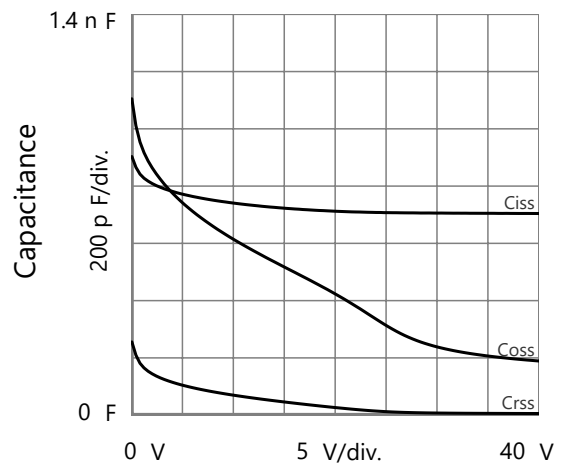
Gate to Source Voltage  
Drain to Source Resistance vs. Gate to Source Voltage



Drain Current  
Drain to Source Resistance vs. Drain Current

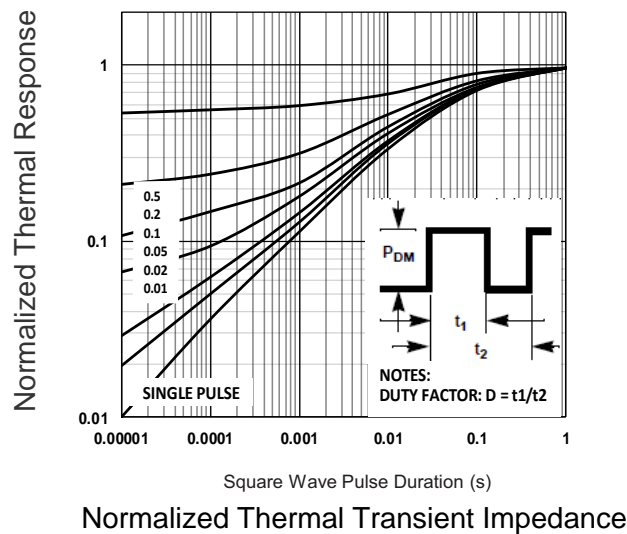
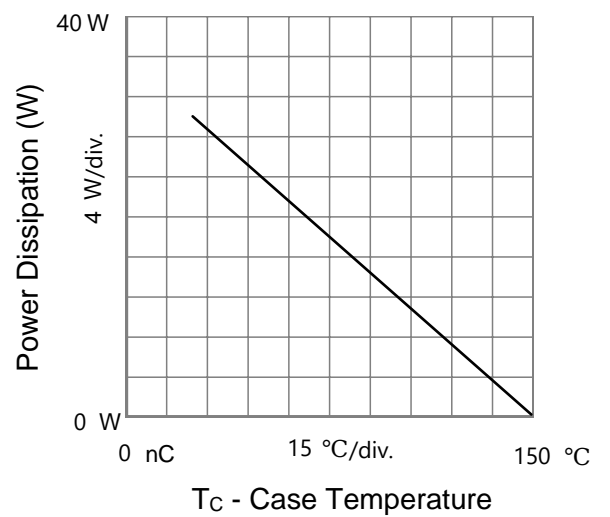
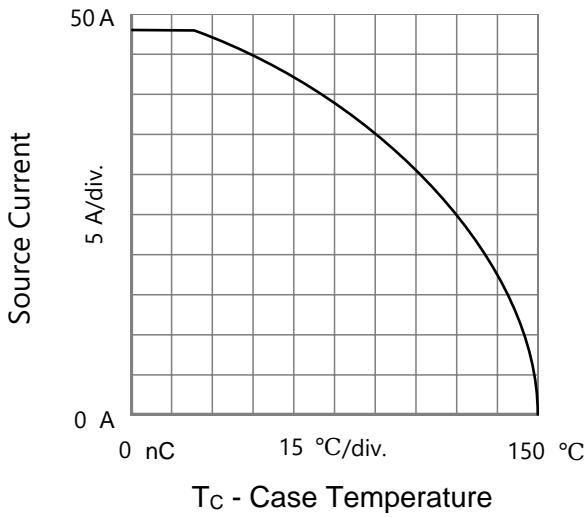
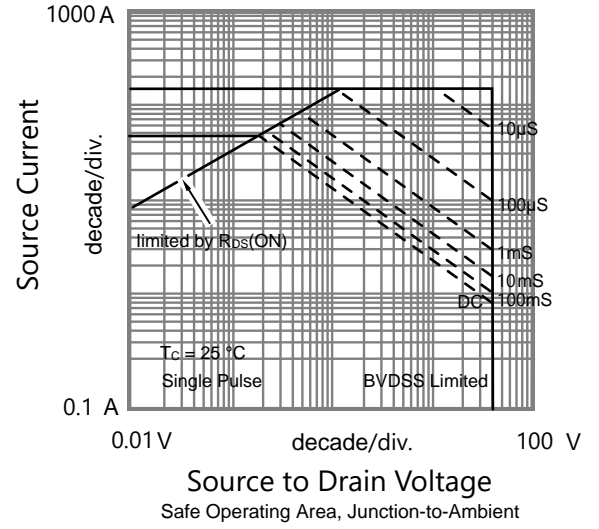
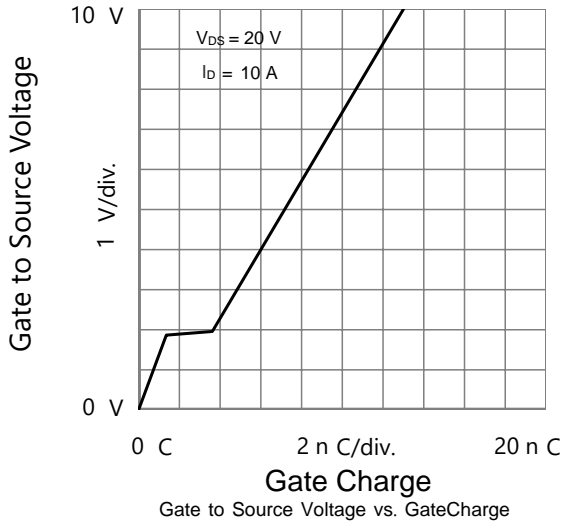


Source to Drain Voltage  
Body Diode Forward Characteristics

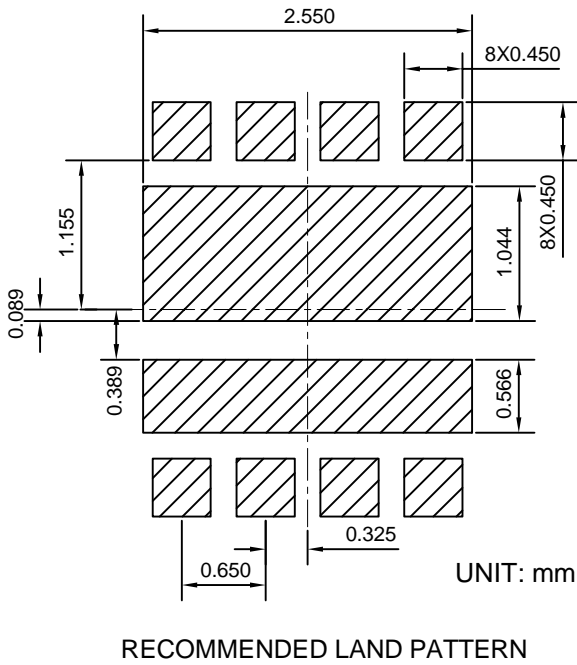
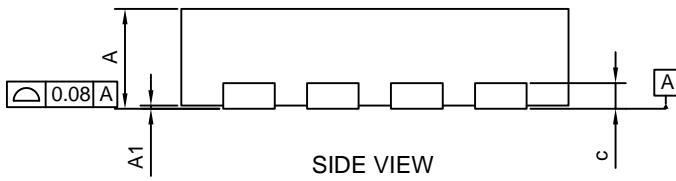
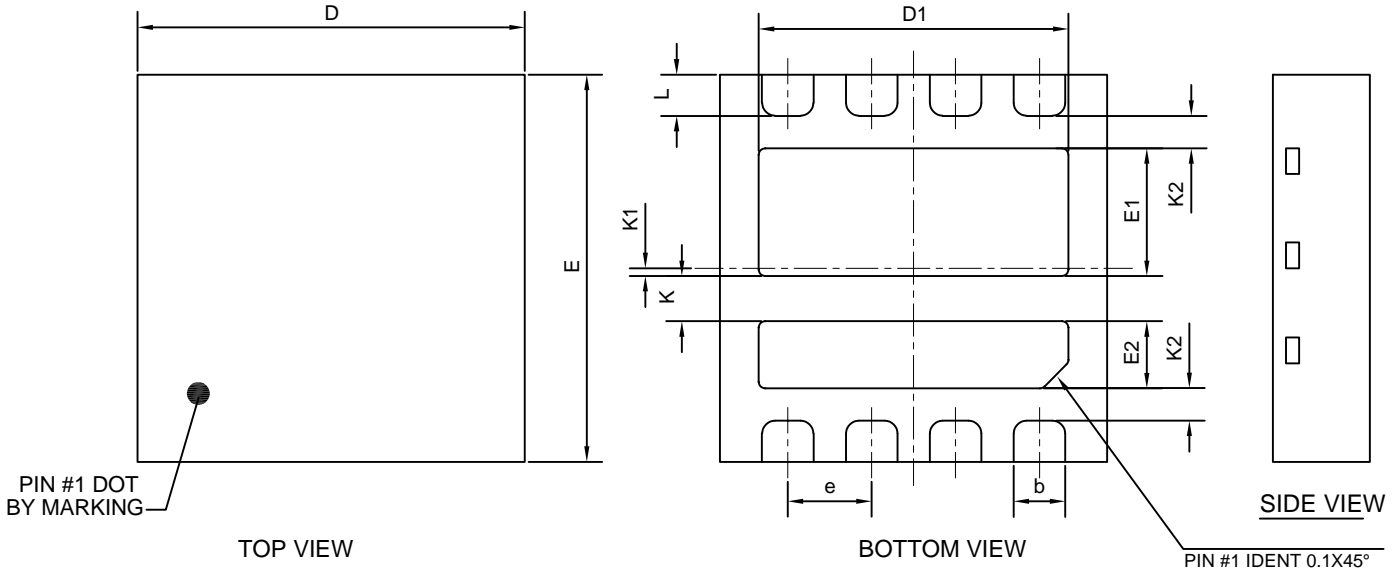


Drain to Source Voltage  
Capacitances

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**DFN3X3-8L-D PACKAGE OUTLINE**



SYMBOLS	DIMENSIONS IN MILLIMETERS		
	MIN	TYP	MAX
A	0.70	0.75	0.80
A1	0.00	-	0.05
c	0.203 REF.		
b	0.35	0.40	0.45
D	2.90	3.00	3.10
D1	2.30	2.40	2.50
E	2.90	3.00	3.10
E1	0.89	0.99	1.09
E2	0.42	0.52	0.62
e	0.65 BSC		
L	0.27	0.32	0.37
K	0.35 REF.		
K1	0.06 REF.		
K2	0.25 REF.		

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